

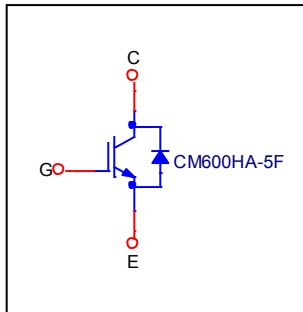
Device Modeling Report

COMPONENTS: Insulated Gate Bipolar Transistor (IGBT)
PART NUMBER: CM600HA-5F
MANUFACTURER: MITSUBISHI
*REMARK: Free-Wheeling Diode Standard Model

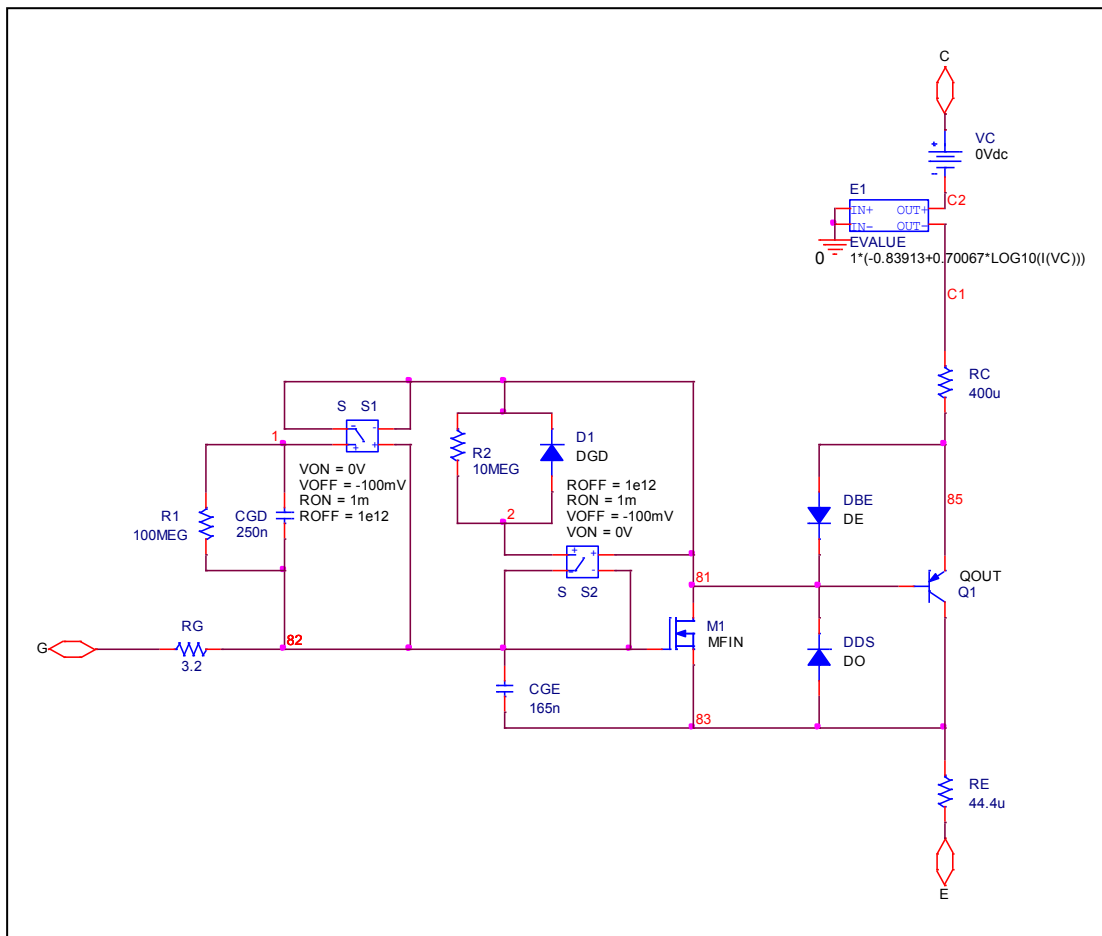


Bee Technologies Inc.

Circuit Configuration

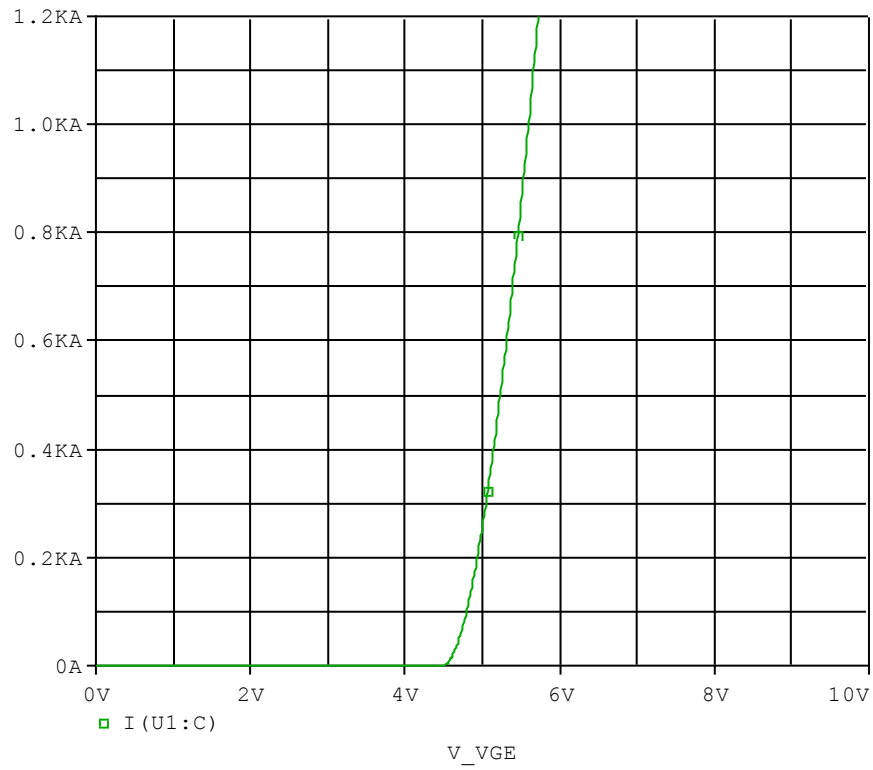


IGBT Subcircuit

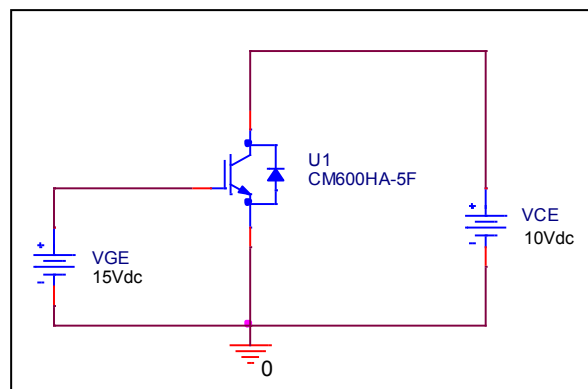


Transfer Characteristics

Circuit Simulation result

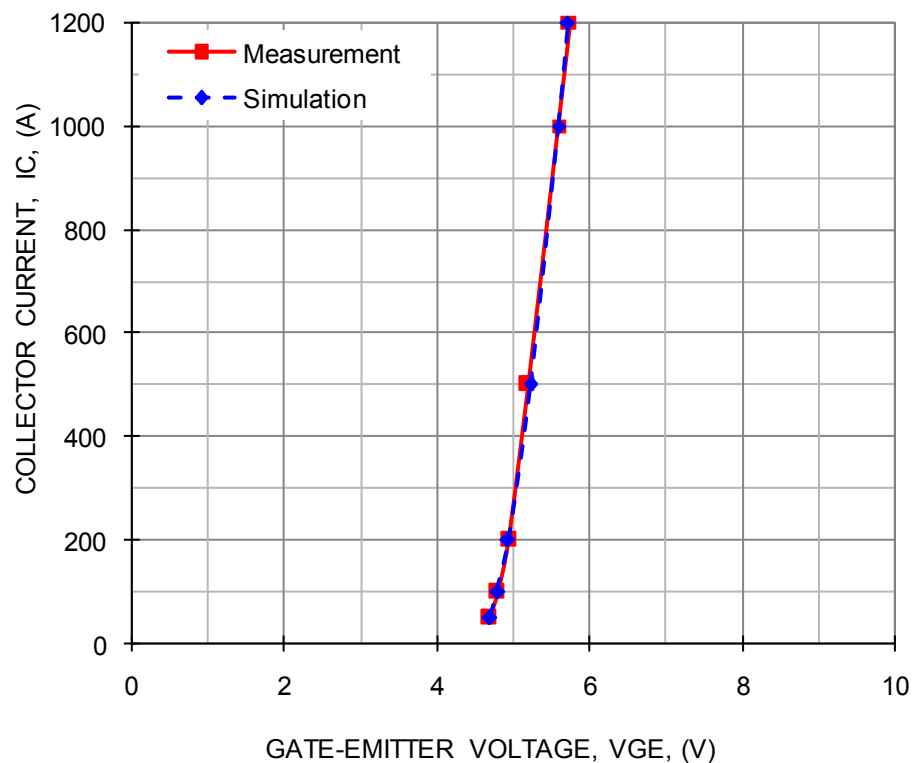


Evaluation circuit



Comparison Graph

Circuit Simulation Result



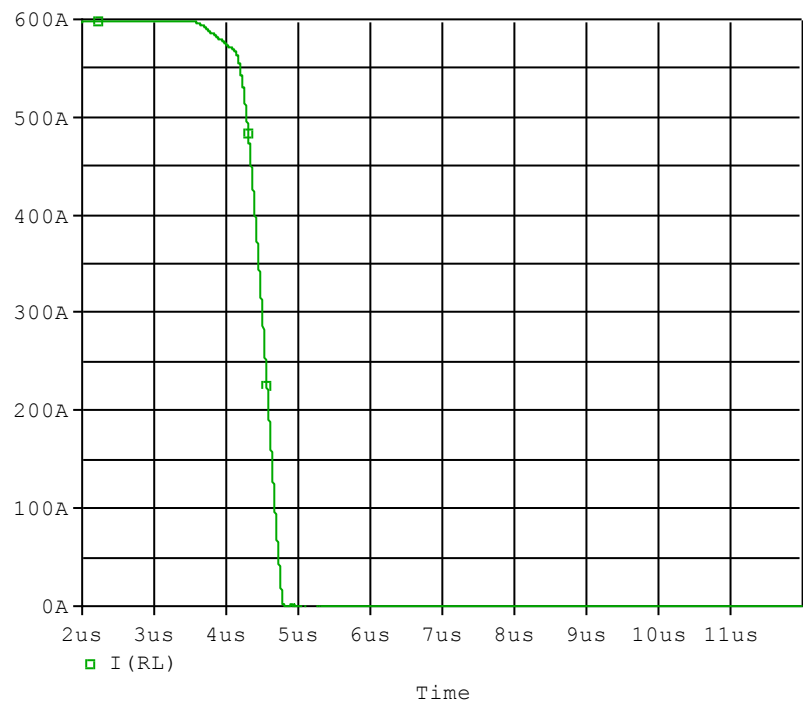
Simulation Result

Test condition: $V_{CE} = 10\text{ V}$

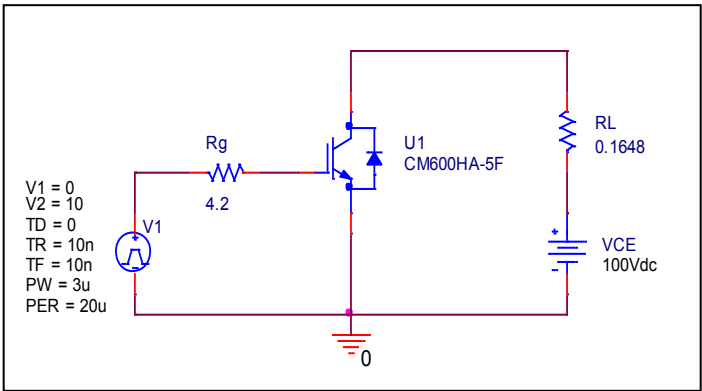
IC (A)	VGE (V)		Error (%)
	Measurement	Simulation	
50	4.700	4.698	-0.04
100	4.800	4.793	-0.14
200	4.950	4.934	-0.33
500	5.200	5.231	0.60
1000	5.600	5.597	-0.05
1200	5.750	5.724	-0.45

Fall Time Characteristics

Circuit Simulation result



Evaluation circuit

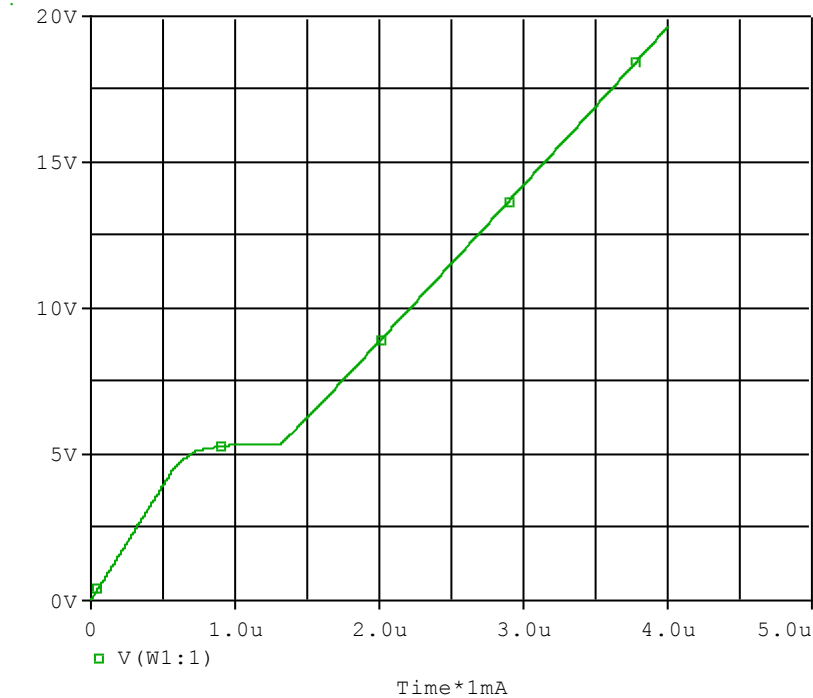


Test condition $I_c=600$ (A), $V_{cc}=100$ (V)

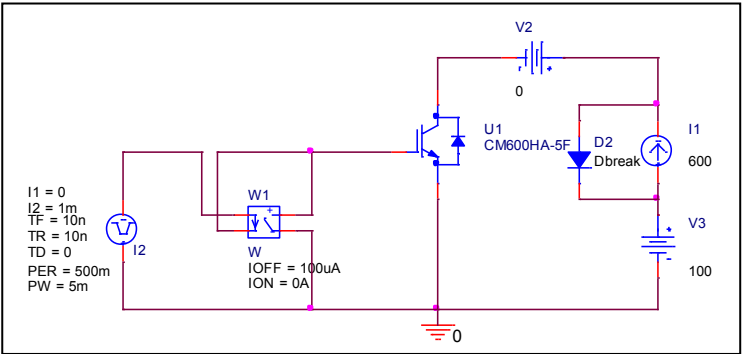
Parameter	Unit	Measurement	Simulation	Error
tf	ns	500.000	499.790	-0.042

Gate Charge Characteristics

Circuit Simulation result



Evaluation circuit

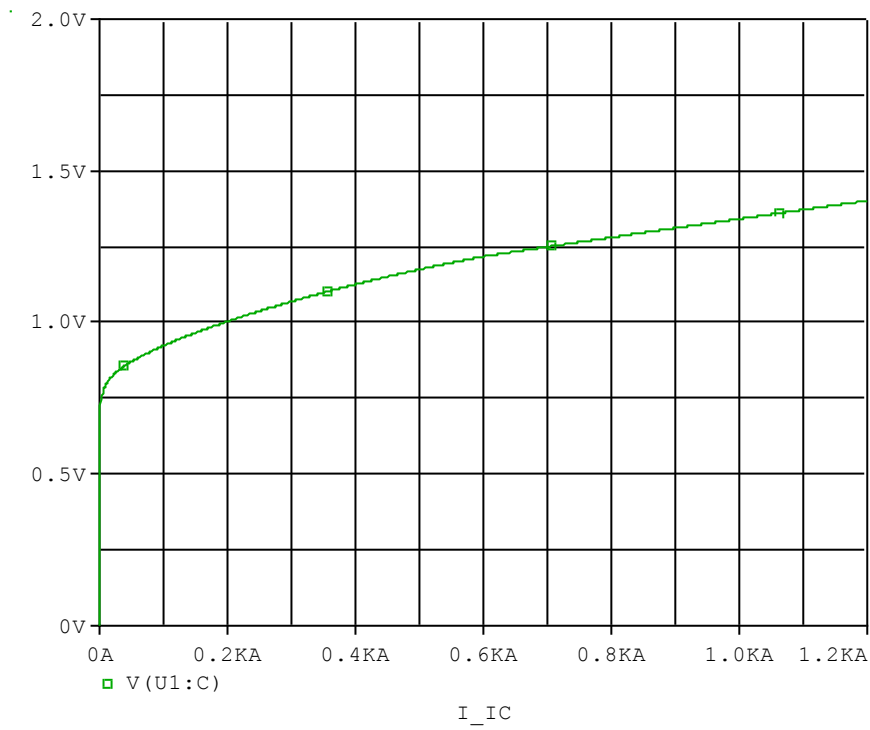


Test condition: $V_{CC}=100\text{ (V)}$, $I_C=600\text{ (A)}$, $V_{GE}=10\text{ (V)}$

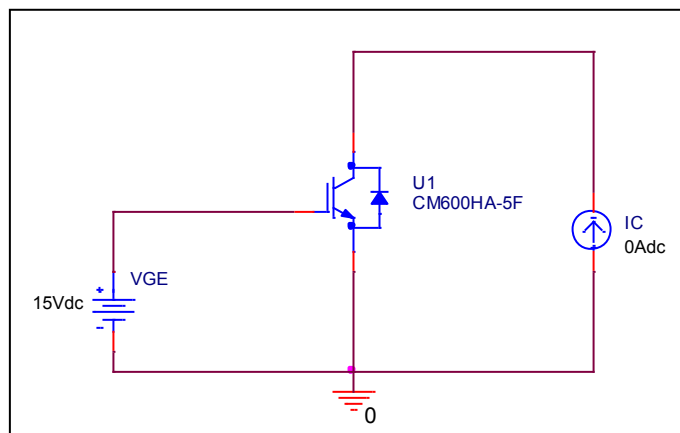
Parameter	Unit	Measurement	Simulation	Error(%)
Qge	nc	625.000	624.550	-0.072
Qgc	nc	850.000	828.036	-2.584
Qg	nc	2200.000	2212.300	0.559

Saturation Characteristics

Circuit Simulation result

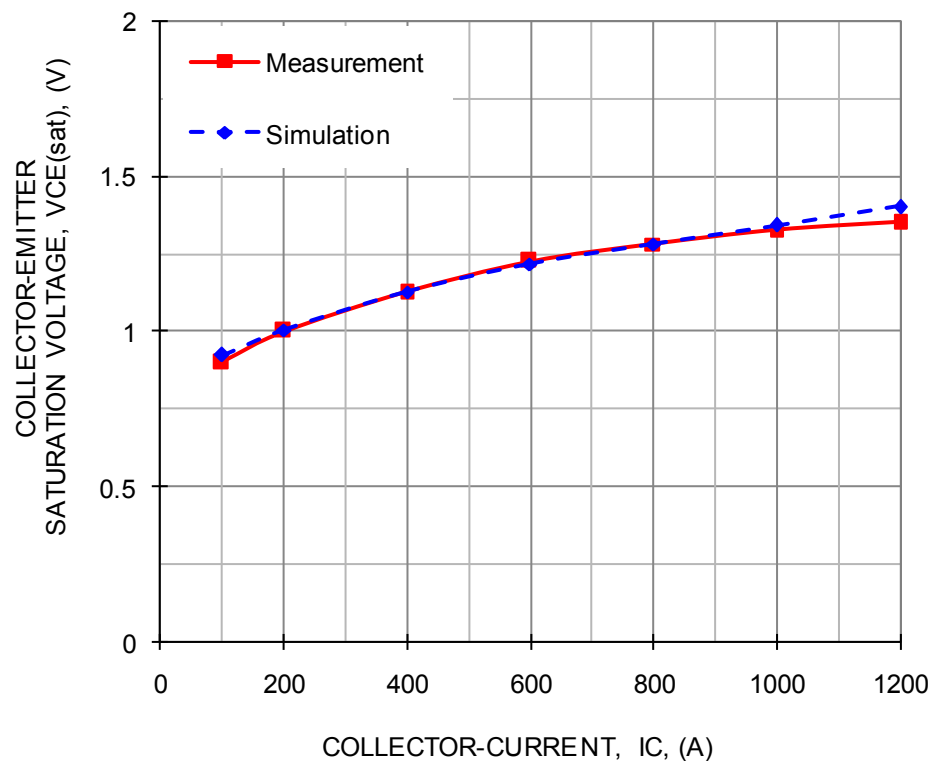


Evaluation circuit



Comparison Graph

Circuit Simulation Result



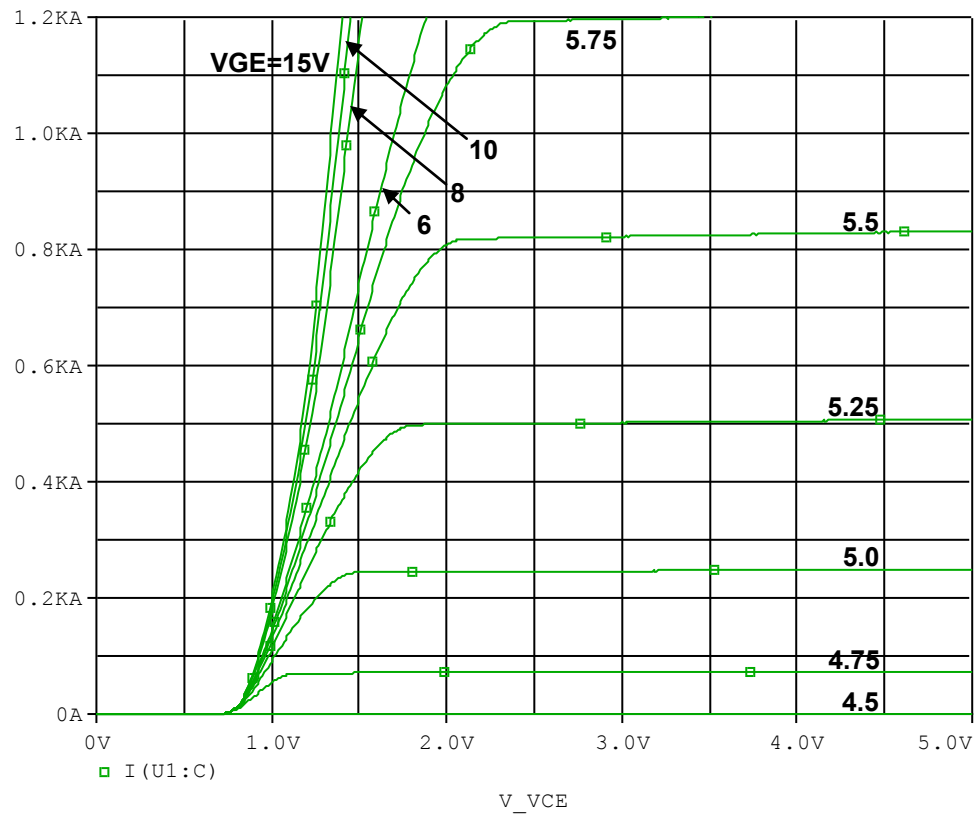
Simulation Result

Test condition: $V_{GE} = 15\text{ V}$

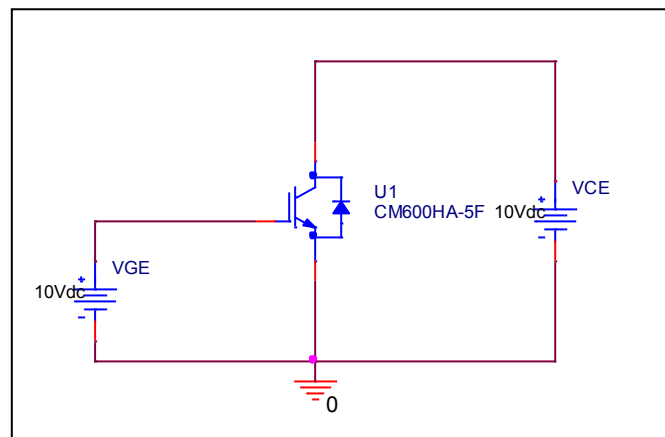
Ic(A)	VCE (V)		Error (%)
	Measurement	Simulation	
100	0.900	0.923	2.59
200	1.000	1.003	0.33
400	1.125	1.126	0.04
600	1.225	1.217	-0.63
800	1.280	1.280	0.02
1000	1.325	1.341	1.24
1200	1.350	1.401	3.80

Output Characteristics

Circuit Simulation result

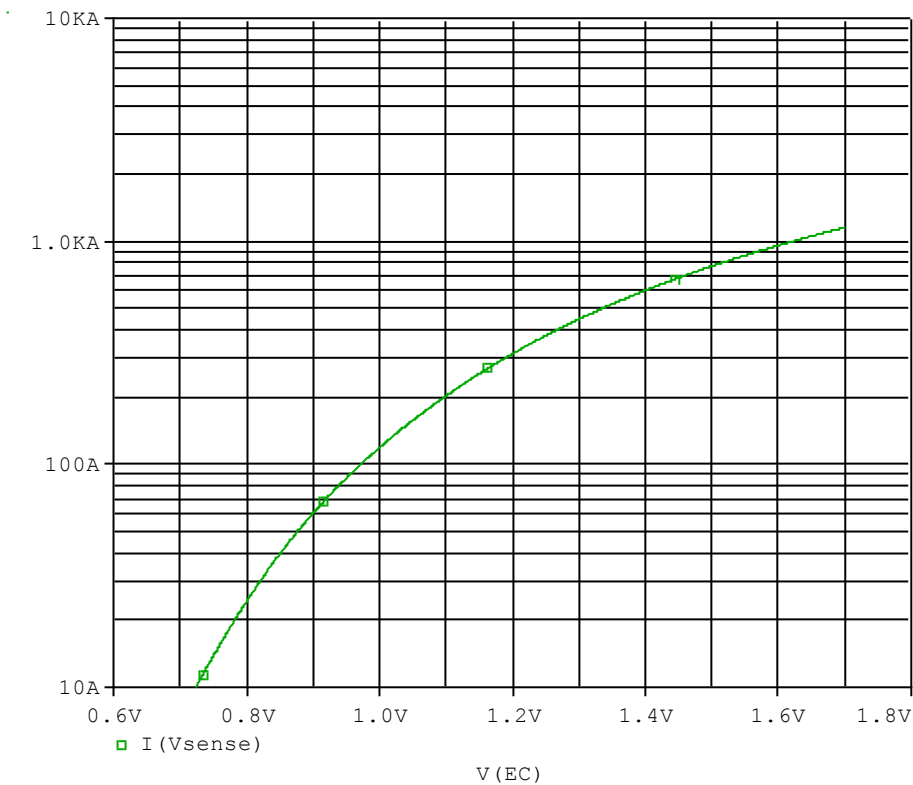


Evaluation circuit

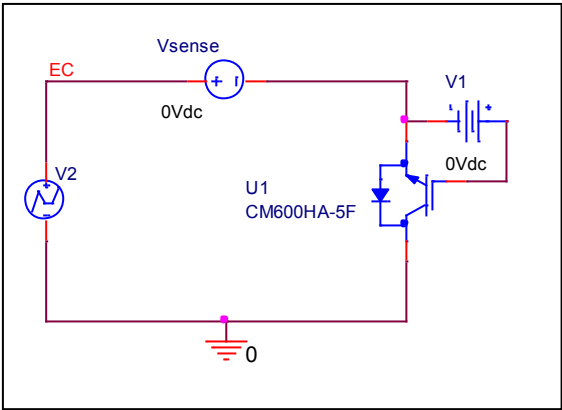


Forward Current Characteristic

Circuit Simulation Result

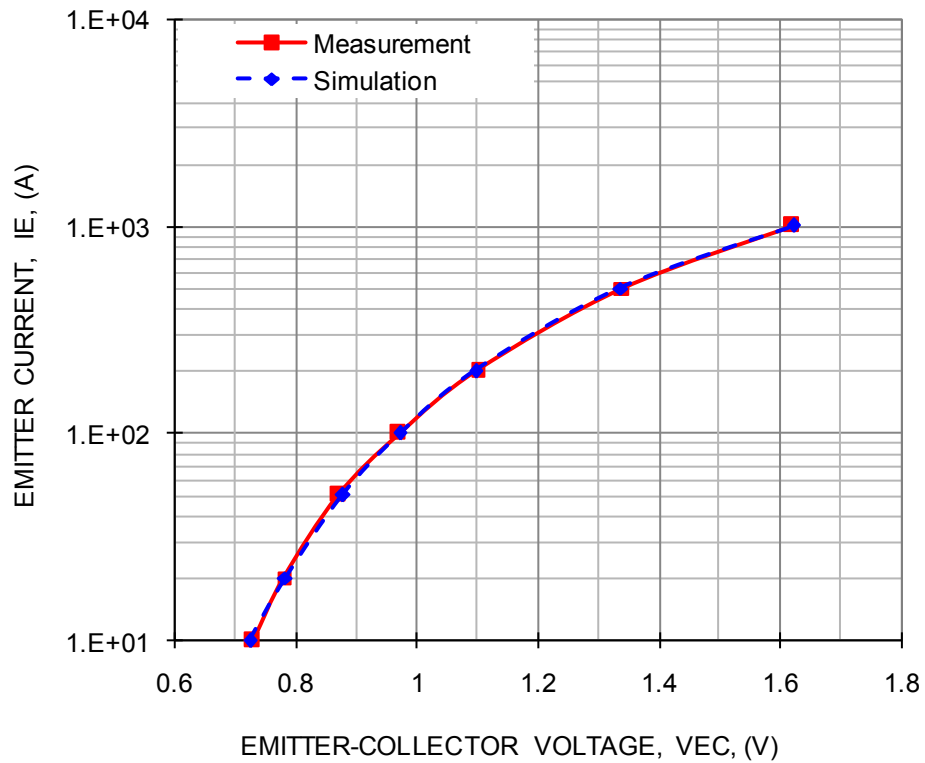


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

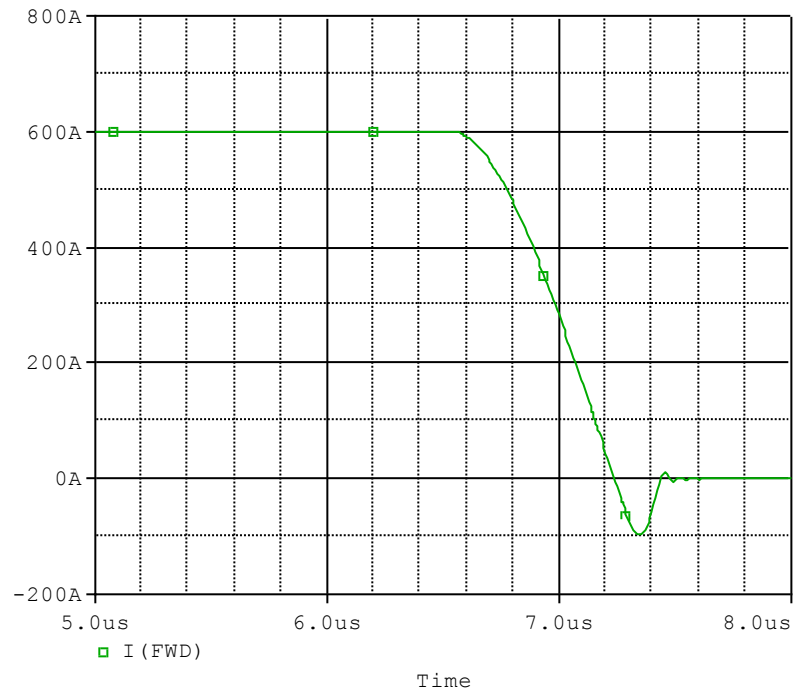


Simulation Result

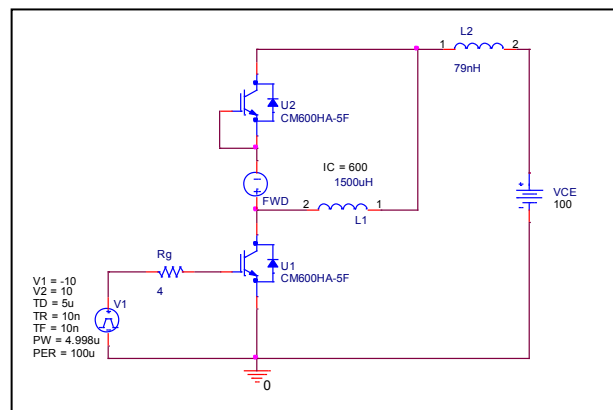
IE(A)	VEC(V)		%Error
	Measurement	Simulation	
10	0.730	0.724	-0.87
20	0.780	0.782	0.28
50	0.870	0.877	0.80
100	0.970	0.972	0.22
200	1.100	1.097	-0.24
500	1.340	1.336	-0.34
1000	1.620	1.622	0.14

Reverse Recovery Characteristics

Circuit Simulation result



Evaluation circuit



Test condition: $V_{CC}=100$ (V), $I_C=600$ (A) , $V_{GE}=\pm 10$ (V)

Parameter	Unit	Measurement	Simulation	Error(%)
trr	nsec	200.000	193.725	-3.14
lrr	A	97.000	97.291	0.30